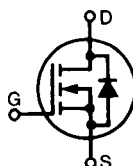


# MegaMOS™ FET

	$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
IXTH / <del>IXTM</del> 11N80	800 V	11 A	0.95 $\Omega$
IXTH / <del>IXTM</del> 13N80	800 V	13 A	0.80 $\Omega$

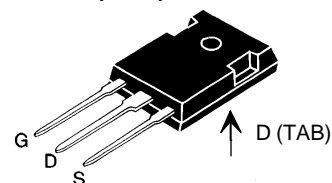
N-Channel Enhancement Mode

Obsolete:  
IXTM11N80  
IXTM13N80



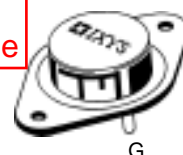
Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	800	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	800	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	11N80	11 A
		13N80	13 A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	11N80	44 A
		13N80	52 A
$P_D$	$T_C = 25^\circ\text{C}$	300	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD (IXTH)



~~TO-204 AA (IXTM)~~

Package  
unavailable



G = Gate,  
S = Source,  
D = Drain,  
TAB = Drain

## Features

- International standard packages
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance (< 5 nH)
  - easy to drive and to protect
- Fast switching times

## Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

## Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 3\text{ mA}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100\text{ nA}$
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$			250 $\mu\text{A}$
	$V_{GS} = 0\text{ V}$			1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 0.5\text{ }I_{D25}$ Pulse test, $t \leq 300\text{ }\mu\text{s}$ ,	11N80		0.95 $\Omega$
		13N80		0.80 $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ , pulse test	8	14	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF
$C_{oss}$			310	pF
$C_{rss}$			65	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$ , (External)		20	50 ns
$t_f$			33	50 ns
$t_{d(off)}$			63	100 ns
$t_f$			32	50 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		145	170 nC
$Q_{gs}$			30	45 nC
$Q_{gd}$			55	80 nC
$R_{thJC}$			0.42	K/W
$R_{thCK}$			0.25	K/W

**Source-Drain Diode**

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$	11N80 13N80		11 A 13 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$	11N80 13N80		44 A 52 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		800	ns

**TO-247 AD (IXTH) Outline**

Terminals: 1 - Gate    2 - Drain  
3 - Source    Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

**TO-204AA (IXTM) Outline**

Pins: 1 - Gate    2 - Source  
Case - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	6.4	11.4	.250	.450
A <sub>1</sub>		3.42		.135
∅b	.97	1.09	.038	.043
∅D		22.22		.875
e	10.67	11.17	.420	.440
e <sub>1</sub>	5.21	5.71	.205	.225
L	7.93		.312	
∅p	3.84	4.19	.151	.165
∅p <sub>1</sub>	3.84	4.19	.151	.165
q	30.15	BSC	1.187	BSC
R		13.33		.525
R <sub>1</sub>		4.77		.188
s	16.64	17.14	.655	.675

Fig. 1 Output Characteristics

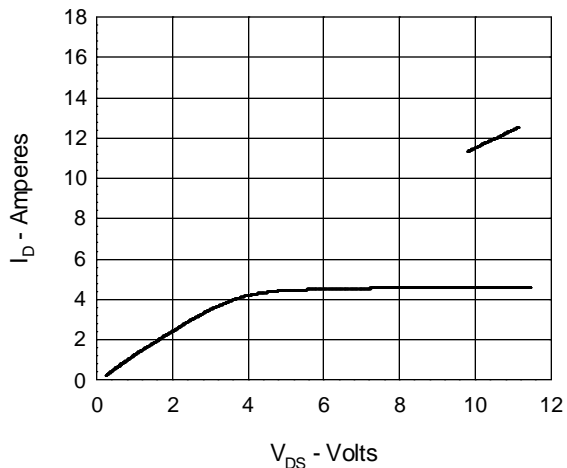


Fig. 2 Input Admittance

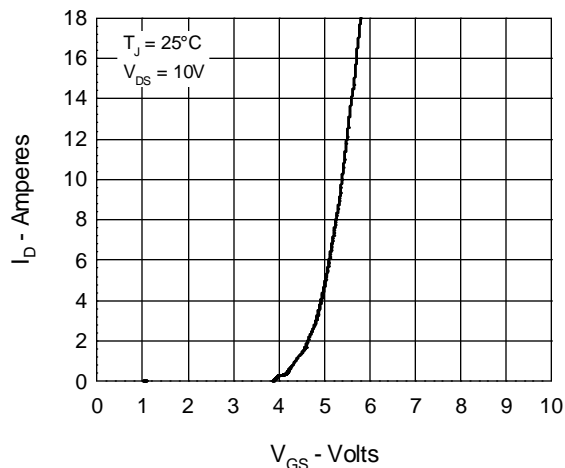


Fig. 3  $R_{DS(on)}$  vs. Drain Current

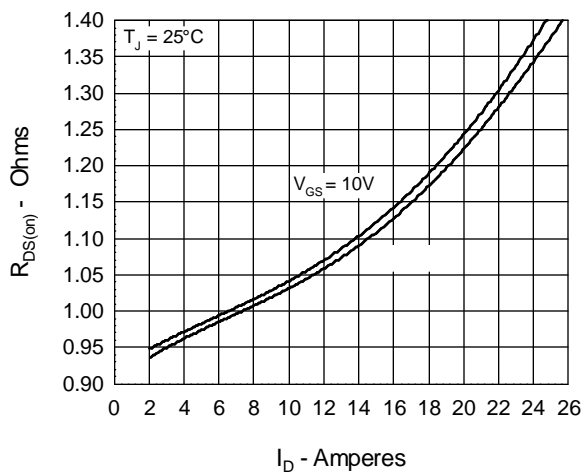


Fig. 4 Temperature Dependence of Drain to Source Resistance

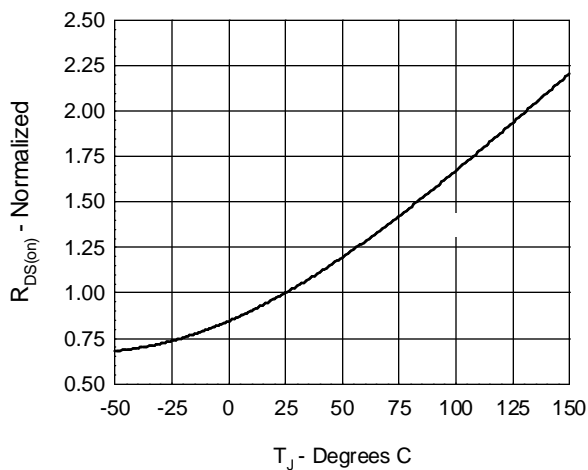


Fig. 5 Drain Current vs. Case Temperature

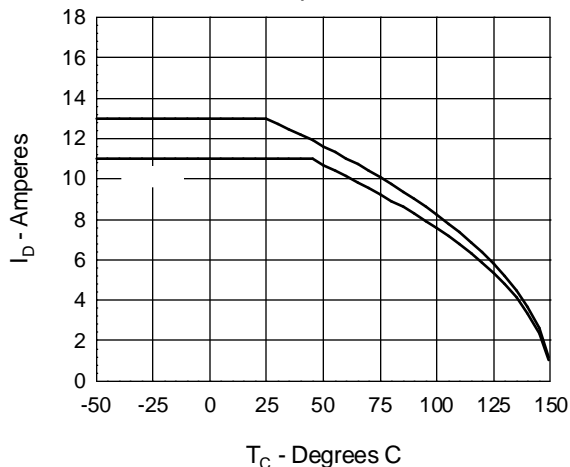
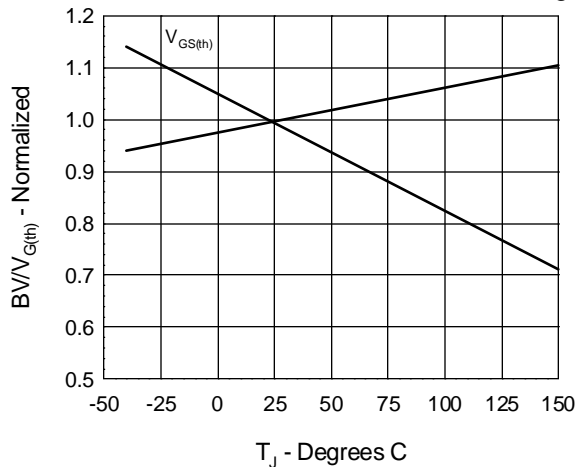
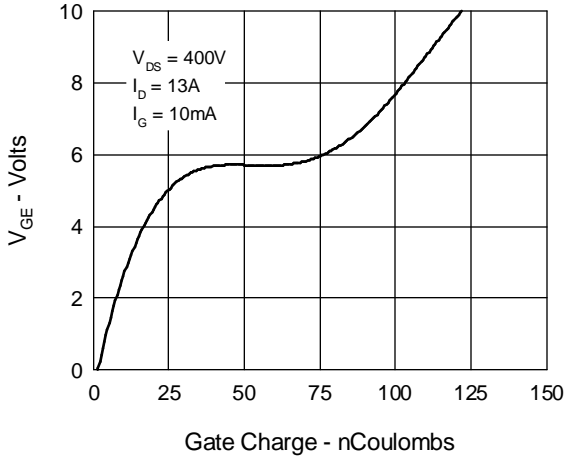


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

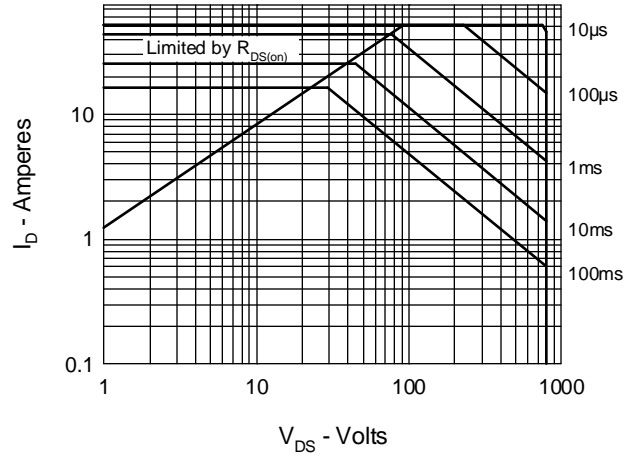


IXYS reserves the right to change limits, test conditions, and dimensions.

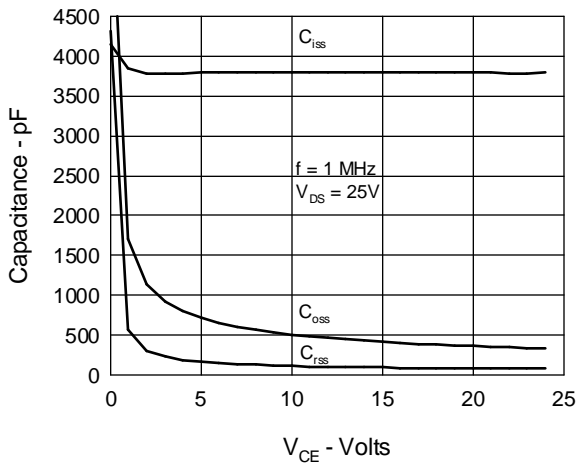
**Fig.7 Gate Charge Characteristic Curve**



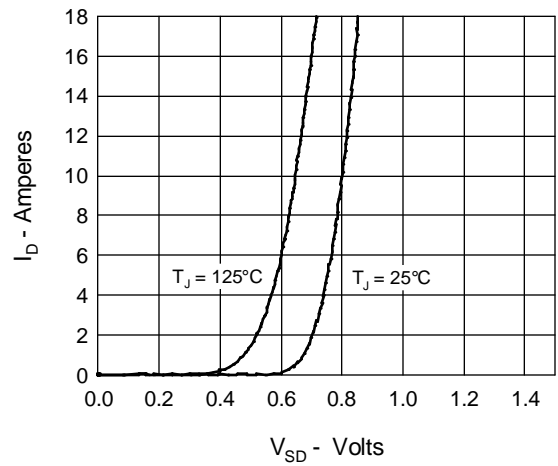
**Fig.8 Forward Bias Safe Operating Area**



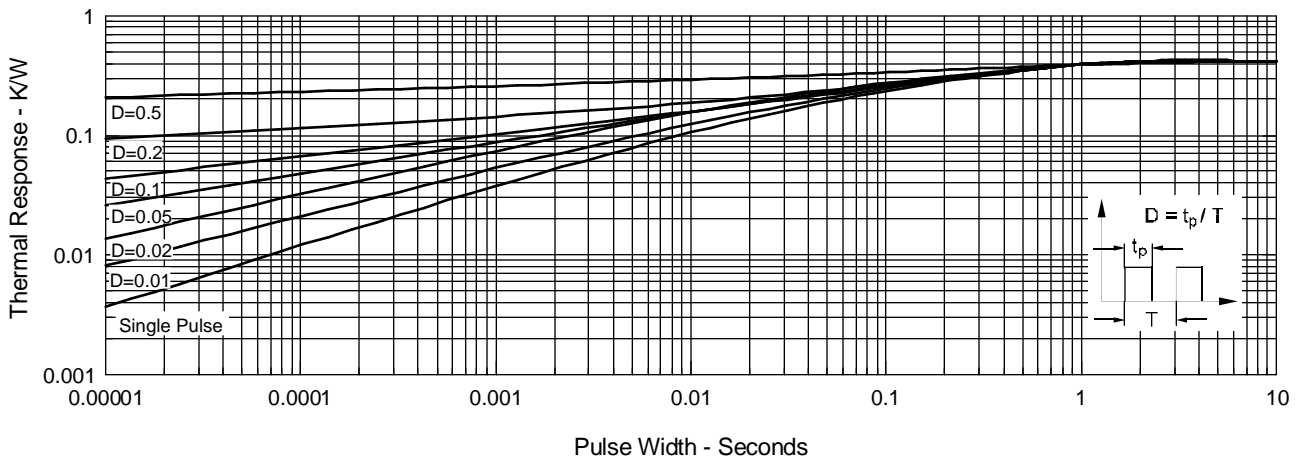
**Fig.9 Capacitance Curves**



**Fig.10 Source Current vs. Source to Drain Voltage**



**Fig.11 Transient Thermal Impedance**





---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).